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Correction: Large-area thin-film synthesis of photoactive Cu₃PS₄ thiophosphate semiconductor with 0–14 pH stability range

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Correction for 'Large-area thin-film synthesis of photoactive Cu₃PS₄ thiophosphate semiconductor with 0–14 pH stability range' by Lena A. Mittmann *et al.*, *Chem. Sci.*, 2025, 16, 21862–21873, <https://doi.org/10.1039/D5SC05882A>.

The original version of this article contained typographical errors in the following section of text:

At the CBM, the dominant antibonding interactions are between S 3p states and P 4s states, with a higher P 4s character at the Γ point than at the CBM on the Γ -X path. Again, the situation is analogous to S 3p/In 6s mixing at the CBM of chalcopyrites and S 3p/Sn 6s mixing in kesterites, pointing to the similar role of P, In, and Sn across these copper-based sulfides, and to phosphorus behaving much like a post-transition metal cation.

Here, P 4s should be P 3s, In 6s should be In 5s and Sn 6s should be Sn 5s. This typographical error does not affect any of the conclusions drawn within the manuscript.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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